

2.28mm Silicon PD Chip datasheet

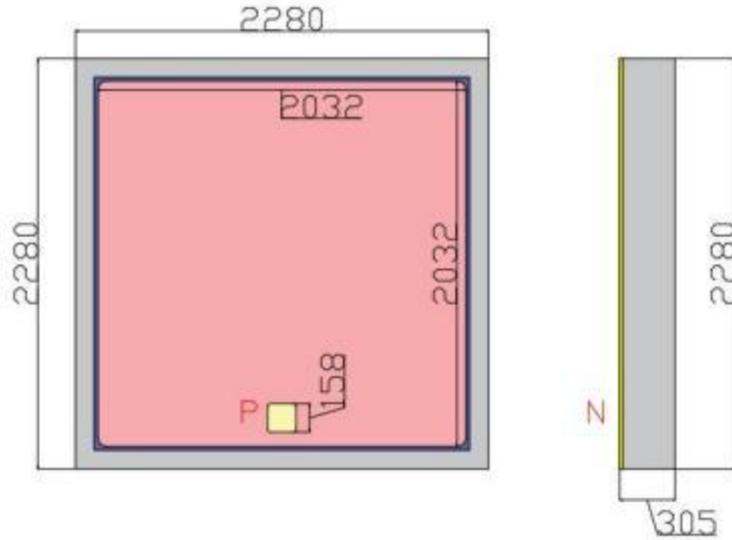
P/N : WS9C-01C

Application

Si PIN photodiode chip

Structure

Planar type : PIN diode
 Electrodes :
 Back side (Cathode) : Au
 Top side (Anode) : Al



DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	2032 x 2032 ± 10			μm
Chip width	2280			μm
Chip length	2280			μm
Chip height	290	305	320	μm
Pad Area		158		μm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.7		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Reverse Dark Current	Id	Vr=10V			10	nA
Sensitive Wavelength Range	λ		400	940	1100	nm
Capacitance	Cj	VR=3V, f=1MHz		30		pF